N-Channel 100-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:

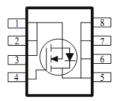
- · LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)	
100	18 @ V _{GS} = 10V	28	
	24 @ V _{GS} = 4.5V	25	



FREE





ABSOLUTE MAXIMUM RATINGS (TA = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage		V_{DS}	100	V		
Gate-Source Voltage		V_{GS}	±20	V		
	T _C =25°C		28 ^c	A		
Continuous Drain Current	T _C =70°C	I _D	23 ^c			
Continuous Drain Current	T _A =25°C		11 ^a			
	T _A =70°C		8.7 ^a			
Pulsed Drain Current ^b		I _{DM}	40			
Continuous Source Current (Diode Conduction) a		I _S	2			
	T _C =25°C		22	W		
Power Dissipation	T _C =70°C	P_{D}	14			
Prower Dissipation	T _A =25°C	_ ' D	3.5 ^a			
	T _A =70°C		2 ^a			
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	D	35			
IMAXIMUM JUNCTION-TO-AMBIENT	Steady State	$R_{\theta JA}$	81	°C/W		
Maximum Junction-to-Case	Steady State	$R_{ heta JC}$	6			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature
- c. Package limited

Electrical Characteristics

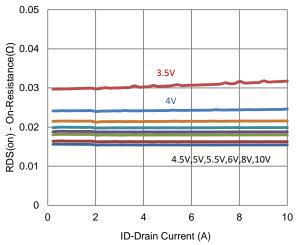
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	1				
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	17			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_{D} = 6 \text{ A}$			18	mO.	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$			24	mΩ	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 6 \text{ A}$		21		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.77		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V},$		11		nC	
Gate-Source Charge	Q_{gs}	$I_{DS} = 50 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 6 \text{ A}$		4.1			
Gate-Drain Charge	Q_{gd}	1D = 0 / X		3.9			
Turn-On Delay Time	t _{d(on)}	V 50 V B = 9.3 O		5			
Rise Time	t _r	$V_{DS} = 50 \text{ V}, R_{L} = 8.3 \Omega,$ $I_{D} = 6 \text{ A},$		6		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		26		ns	
Fall Time	t _f	VGEN = 10 V, NGEN 0 12		15			
Input Capacitance	C_{iss}			828			
Output Capacitance	C_{oss}	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		153		pF	
Reverse Transfer Capacitance	C_{rss}			26]	

Notes

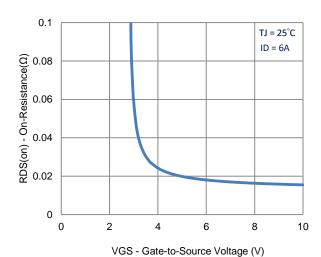
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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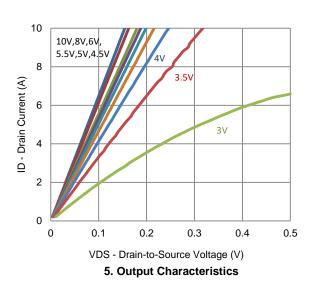
Typical Electrical Characteristics

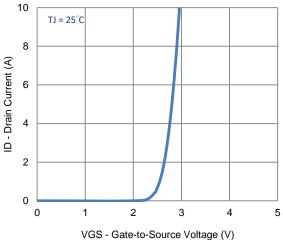


1. On-Resistance vs. Drain Current

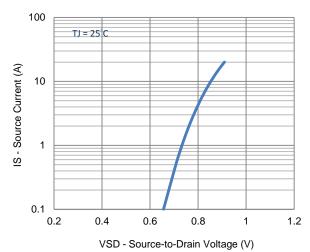


3. On-Resistance vs. Gate-to-Source Voltage

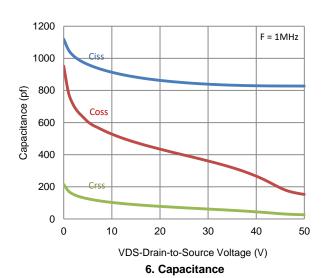




2. Transfer Characteristics

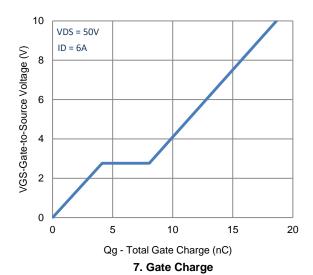


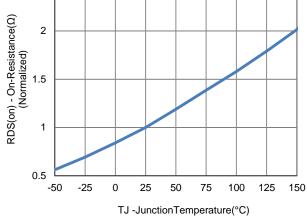
4. Drain-to-Source Forward Voltage

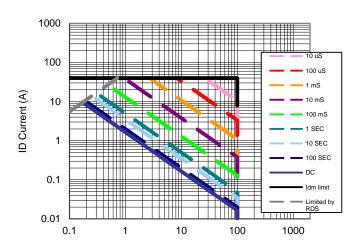


Typical Electrical Characteristics

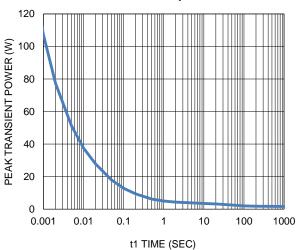
2.5







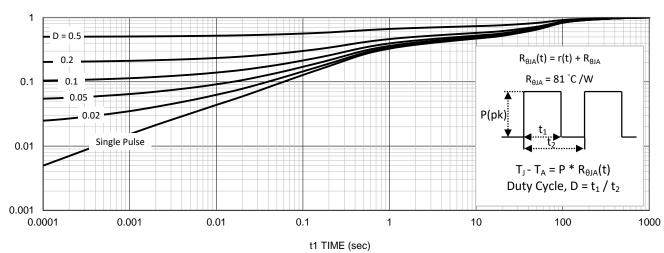
8. Normalized On-Resistance Vs Junction Temperature



VDS Drain to Source Voltage (V)

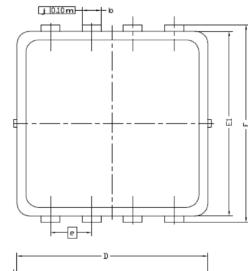
9. Safe Operating Area

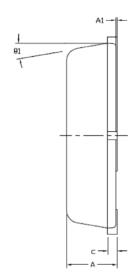
10. Single Pulse Maximum Power Dissipation

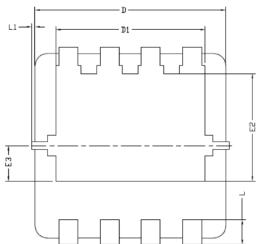


11. Normalized Thermal Transient Junction to Ambient

Package Information







DIM,	MILLIMETERS			INCHES			
	NIM	NDM	MAX	MIN	NDM	MAX	
Α	0,700	0,80	0.900	0,0276	0,0315	0,0354	
A1	0.00		0,05	0,000		0.002	
b	0.24	0.30	0.35	0.009	0.012	0.014	
C	0.10	0.152	0.25	0.004	0.006	0.010	
D	3.00 BSC			0.118 BSC			
D1	2	.35 BS	С	0.093 BSC			
Ε	3.20 BSC			0.126 BSC			
E1	3.00 BSC			0.118 BSC			
E2	1.75 BSC			0.069 BSC			
E3	0,575 BSC			0.023 BSC			
е	0	0.65 BSC			0.026 BSC		
L	0,30	0,40	0,50	0,0118	0,0157	0,0197	
L1	0		0,100	0		0.004	
91	0°	10°	12°	0°	10°	12°	